## Atomic scale compositions across DyScO<sub>3</sub>/SrTiO<sub>3</sub> interfaces

 $\frac{M. Luysberg^{1}}{T. Heeg^{2**}} M. Heidelmann^{1}, L. Houben^{1}, M. Boese^{1*},$  $T. Heeg^{2**} M. Röckerath^{2}, and J. Schubert^{2}$ 

<sup>1</sup>Institute of Solid State Research and Ernst Ruska-Centre for Microscopy and Spectroscopy with Electrons, Research Centre Jülich, D-52425 Jülich, Germany

<sup>2</sup>Institute of Bio- and Nanosystems and JARA-FIT, Research Centre Jülich, D-52425 Jülich, Germany

\*present address: CRANN, Trinity College Dublin \*\*present address: Department of Materials Science and Engineering, Pennsylvania State University, University Park, PA

M.Luysberg@fz-juelich.de

Keywords: perovskite interface, pulsed laser deposition, STEM, EELS

Recently, highly conducting layers were reported at the interfaces between complex, insulating oxides of different polarity [1]. The polar discontinuity delivers the driving force for a charge accumulation in the interfacial region which has been demonstrated for LaAlO<sub>3</sub> interfaces with SrTiO<sub>3</sub>. Here it is shown that the polar discontinuity can be accommodated by variations in composition of cat ion lattice planes at the polar oxide interface between DyScO<sub>3</sub> and SrTiO<sub>3</sub>, where DyScO<sub>3</sub> holds the same polarity as LaAlO<sub>3</sub>. An intermixing extending over two monolayers at the interfaces for both the Dy-Sr sublattice and the Sc-Ti sublattice is quantified. As a result, charge neutrality is established by electrical compensation between neighbouring atomic planes.

The atomic structure of a DyScO<sub>3</sub>/SrTiO<sub>3</sub> multilayer system, which was grown by pulsed laser deposition, is revealed in the HAADF image shown in Figure 1. Along the interfaces, i.e. in atom rows 4 and 14, the contrast at the Dy/Sr positions is clearly observed to alternate between neighbouring atomic columns. This is also seen in the concentration profile shown at the bottom, which was evaluated by quantification of the intensities through two-dimensional Gaussian fits to each atom position. I.e. an ordered interface structure is unambiguously detected, which can only be observed along the [101] direction seen here being one of two possible domain orientations of epitaxially grown DyScO<sub>3</sub> on SrTiO<sub>3</sub> [2].

The Sc and Ti composition of each atomic layer were determined by isochronous recording of EEL spectra (Fig 2 top) and of a HAADF image (fig 2 bottom). Details of the method are described elsewhere [3]. Sc and Ti concentrations are superimposed in the HAADF image in Figure 2. In addition, the average Dy concentration is displayed, i.e. the average of positions A and B shown in Figure 1. An intermixing extending over two monolayers at the interfaces is observed for both the Dy-Sr sublattice and the Sc-Ti sublattice. Furthermore, the valence of Ti is found to be constant throughout the layer system. Employing the ionic model [1], the composition of the individual atomic layers can be translated into charges, which are displayed for the atomic layers 12 through 16 in Fig. 3. Considering compensation between adjacent layers, which is denoted by the arrows, each of the layers is found to be neutral as indicated by the diamonds. Hence, the interfaces are expected to be insulating, which is confirmed by electric measurements [4]. From this result it is concluded that in addition to charge accumulations, intermixing of cat ions can contribute to counteract the interface dipoles associated with the polar discontinuity.

1. Nakagawa N, Hwang HY, Muller DA. Nature Materials 2006;5:204.

- 2. Boese M, Heeg T, Schubert J, Luysberg M. Journal of Materials Science 2006; 41:4434
- 3. Heidelmann M. et al., Proc. 14th EMC 2008; 1: 383, DOI: 10.1007/978-3-540-85156-1\_12

4. Luysberg M et al. Acta Materialia 2009 in press



Figure 1. HAADF image of

SrTiO<sub>3</sub>/DyScO<sub>3</sub> multilayers (top). For each Dy layer the concentrations of positions A and B are deduced (bottom). Error bars denote the standard deviation of five equivalent positions within each Dy layer, i.e. positions A and B, respectively. The interface layers, rows 4 and 14, show a distinct difference in contrast between the neighbouring positions A and B. Hence, an ordered interface structure is formed.



**Figure 2.** The spectroscopic image (top) showing the  $L_{23}$  absorption edges of Sc and Ti versus the lateral position and the HAADF image of SrTiO<sub>3</sub>/DyScO<sub>3</sub> (bottom) were recorded simultaneously. The fast scan direction runs from bottom to top. Superimposed are the Dy (red triangles), Sc (yellow circles) and Ti (yellow open squares) concentrations for each atomic layer, which were obtained from the HAADF image (FIG 1) and the spectra extracted row by row from the spectroscopic image.



**Figure 3.** Summary of charges according to the compositions for layers 12 through16 shown in Figs. 1 and 2. Charge compensation between adjacent layers is indicated by the arrows and the hatching patterns. The resulting charge in each layer is shown as diamond. Error bars are calculated from the error estimates in composition.